NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF839F** is Designed for Class AB, Common Emitter Applicatons Up to 960 MHz.

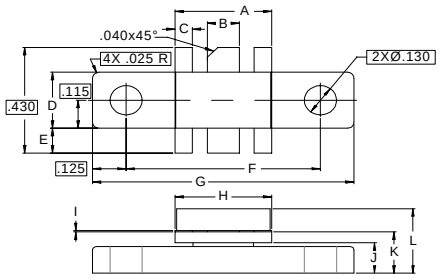
FEATURES INCLUDE:

- Input Matching Network
- High Gain
- Gold Metalization

MAXIMUM RATINGS

I_C	0.6 A
V_{CES}	36 V
P_{DISS}	20 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	9.0 °C/W

PACKAGE STYLE .230 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.355 / 9.02	.365 / 9.27
B	.115 / 2.92	.125 / 3.18
C	.075 / 1.91	.085 / 2.16
D	.225 / 5.72	.235 / 5.97
E	.090 / 2.29	.110 / 2.79
F	.720 / 18.29	.730 / 18.54
G	.970 / 24.64	.980 / 24.89
H	.355 / 9.02	.365 / 9.27
I	.004 / 0.10	.006 / 0.15
J	.120 / 3.05	.130 / 3.30
K	.160 / 4.06	.180 / 4.57
L	.230 / 5.84	.260 / 6.60

1 & 3 & 4 & 6 = EMITTER 2 = BASE
5 = COLLECTOR

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 5.0 mA	40			V
BV_{CEO}	I_C = 5.0 mA	16			V
BV_{EBO}	I_E = 100 µA	3.5			V
I_{CES}	V_{CE} = 15 V			1	mA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	10		150	---
C_{OB}	V_{CB} = 15 V f = 1.0 MHz			10	pF
P_G	V_{CE} = 12.5 V I_{CQ} = 50mA P_{OUT} = 3.0 W	8.0	10.0		dB
η_C	F_O = 870 MHz	50			%

Specifications are subject to change without notice.